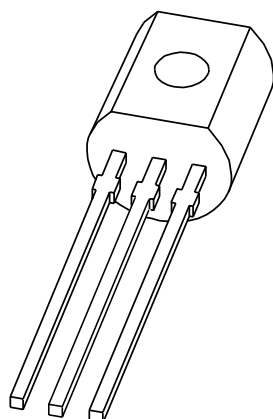


DATA SHEET



BF421; BF423 PNP high voltage transistors

Product specification
Supersedes data of 1996 Dec 09

2004 Nov 10

PNP high voltage transistors

BF421; BF423

FEATURES

- Low feedback capacitance.

APPLICATIONS

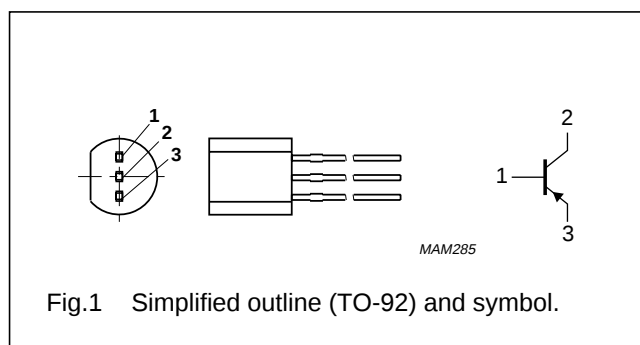
- Class-B video output stages in colour television and professional monitor equipment.

DESCRIPTION

PNP transistors in a TO-92 plastic package.
NPN complements: BF420 and BF422.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF421	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BF423			

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	—300	V
	BF421		—	—250	V
V_{CEO}	collector-emitter voltage	open base	—	—300	V
	BF421		—	—250	V
I_{CM}	peak collector current		—	—100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	—	830	mW
h_{FE}	DC current gain	$V_{CE} = -20\text{ V}; I_C = -25\text{ mA}$	50	—	
C_{re}	feedback capacitance	$V_{CE} = -30\text{ V}; I_C = i_c = 0\text{ A}; f = 1\text{ MHz}$	—	1.6	pF
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -10\text{ mA}; f = 100\text{ MHz}$	60	—	MHz

PNP high voltage transistors

BF421; BF423

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BF421		–	–300	V
	BF423		–	–250	V
V_{CEO}	collector-emitter voltage	open base			
	BF421		–	–300	V
	BF423		–	–250	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–50	mA
I_{CM}	peak collector current		–	–100	mA
I_{BM}	peak base current		–	–50	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	830	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on a printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on a printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -200\text{ V}$; $I_E = 0\text{ A}$	–	–10	nA
		$V_{CB} = -200\text{ V}$; $I_E = 0\text{ A}$; $T_j = 150\text{ °C}$	–	–10	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}$; $I_C = 0\text{ A}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -20\text{ V}$; $I_C = -25\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -30\text{ mA}$; $I_B = -5\text{ mA}$	–	–0.6	V
C_{re}	feedback capacitance	$V_{CE} = -30\text{ V}$; $I_C = i_c = 0\text{ A}$; $f = 1\text{ MHz}$	–	1.6	pF
f_T	transition frequency	$V_{CE} = -10\text{ V}$; $I_C = -10\text{ mA}$; $f = 100\text{ MHz}$	60	–	MHz

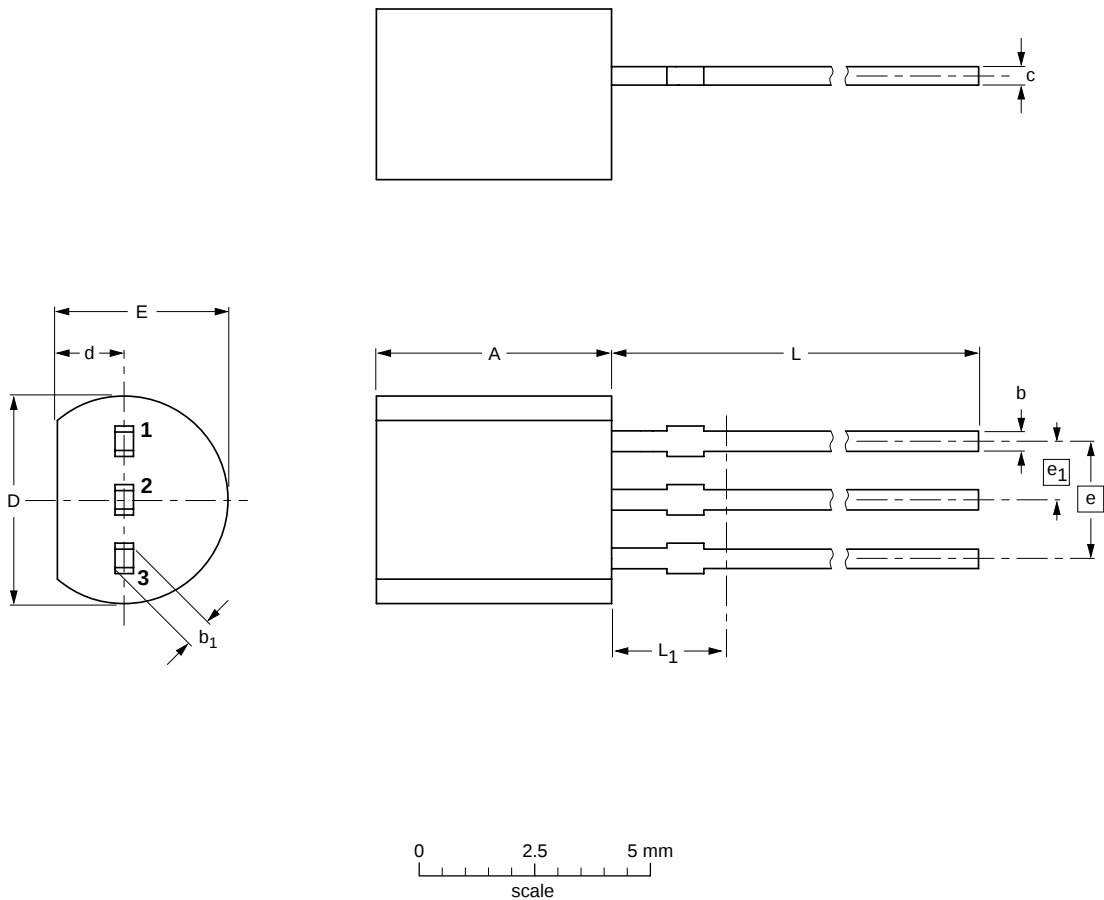
PNP high voltage transistors

BF421; BF423

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			-97-02-28 04-06-28

PNP high voltage transistors

BF421; BF423

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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